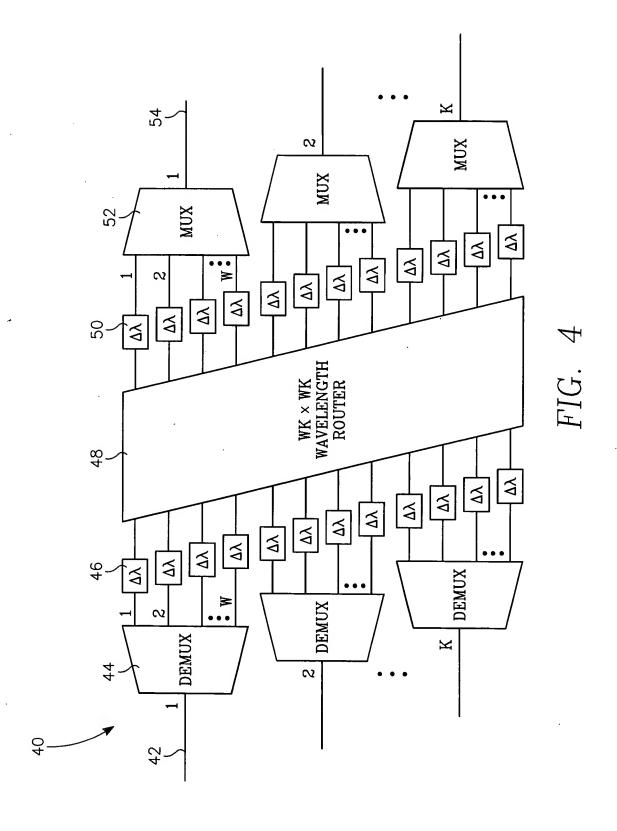
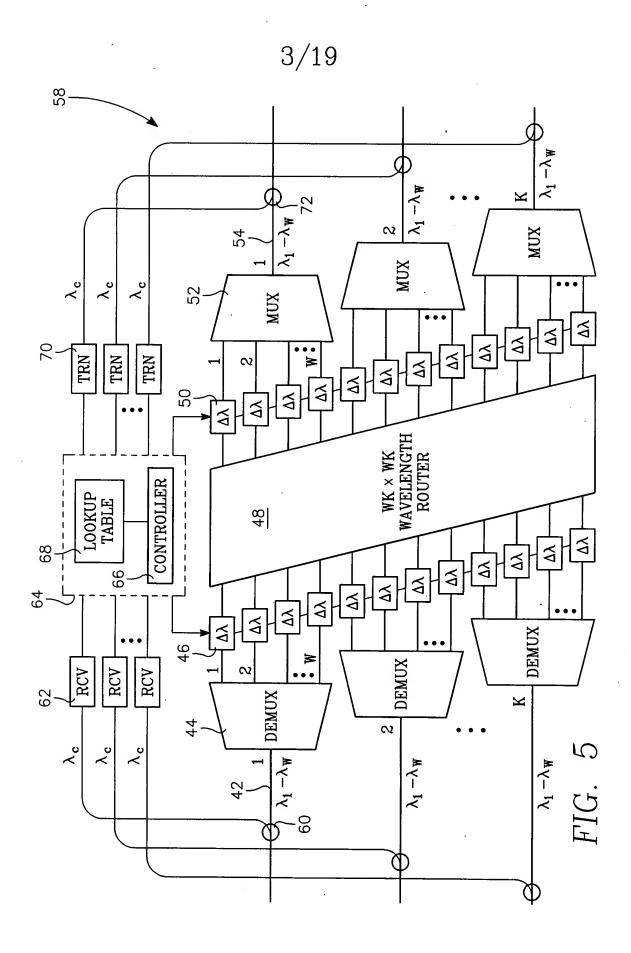
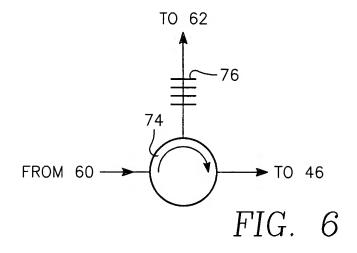


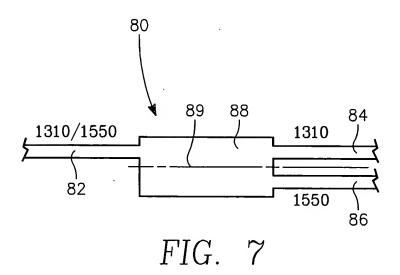
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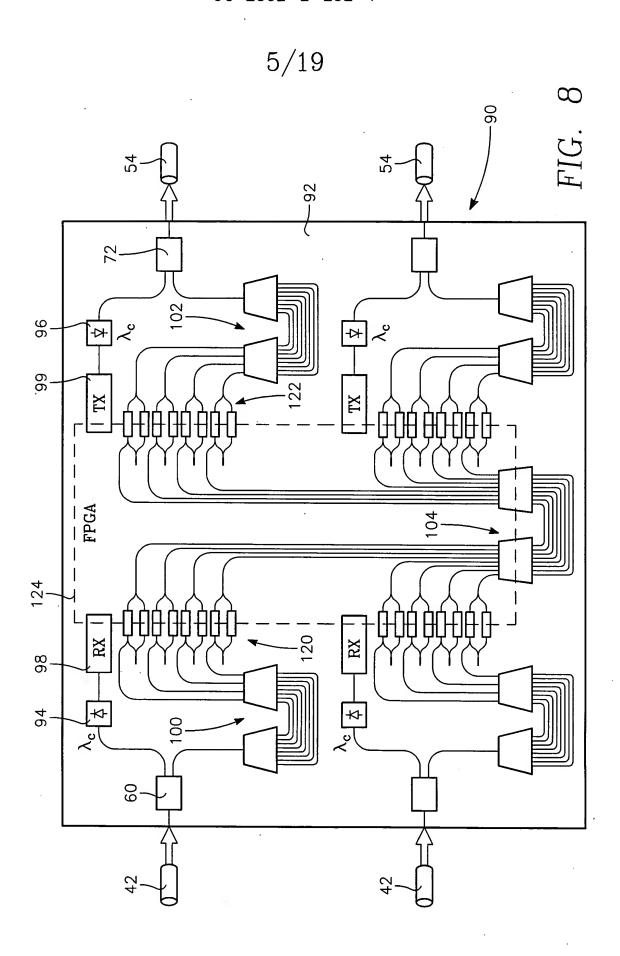




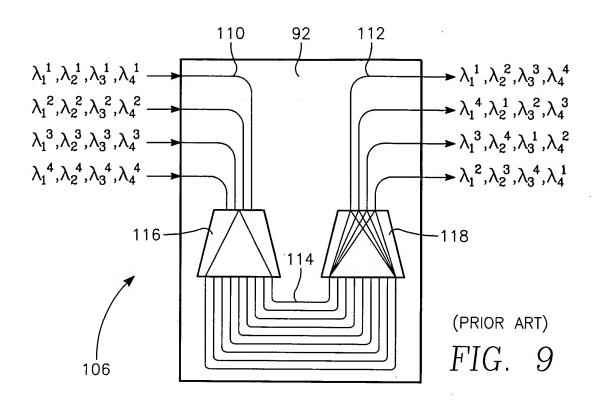
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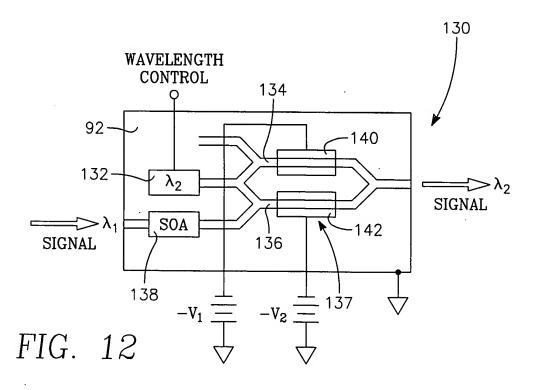


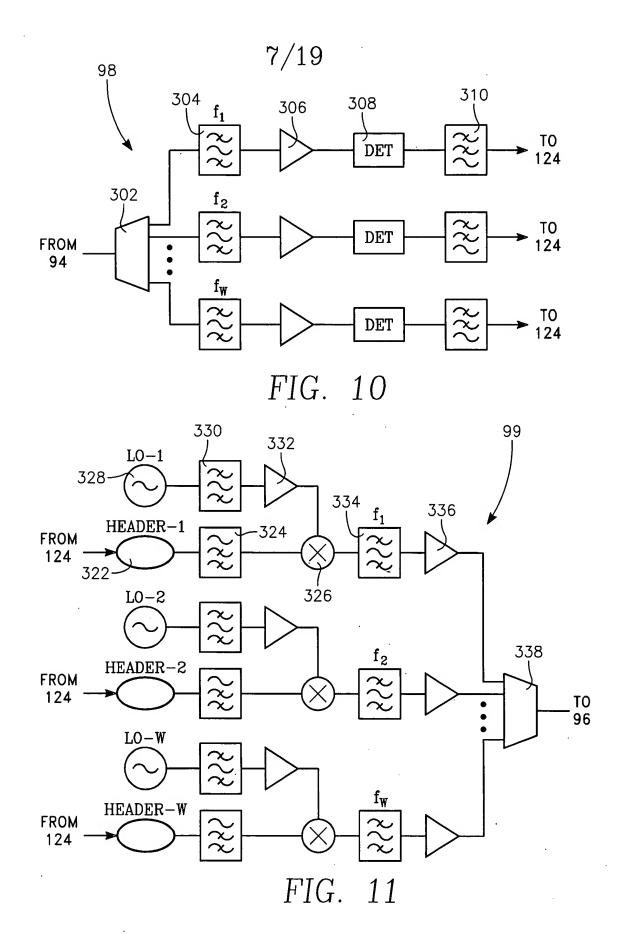




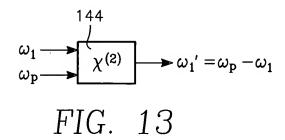
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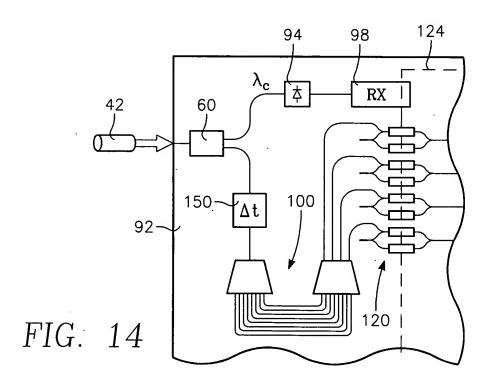


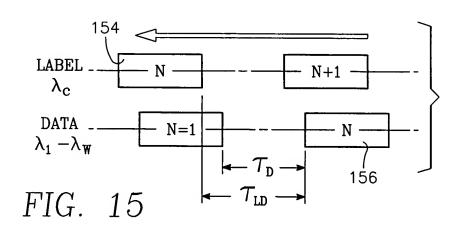




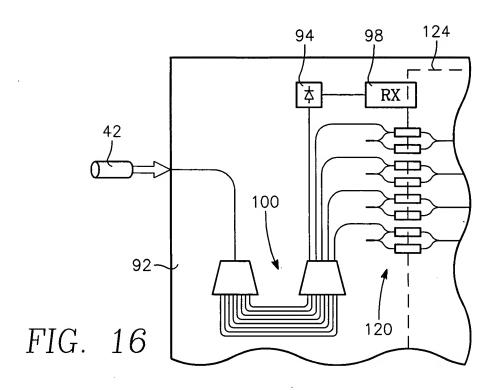


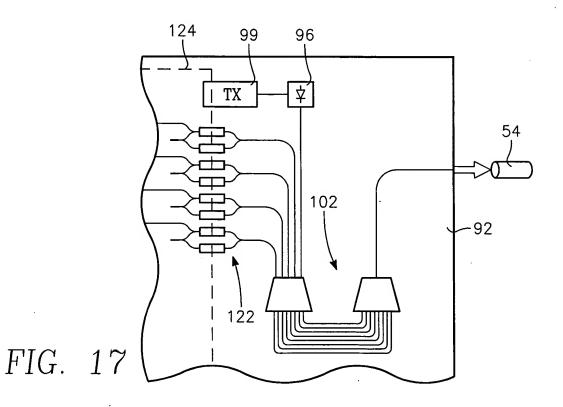






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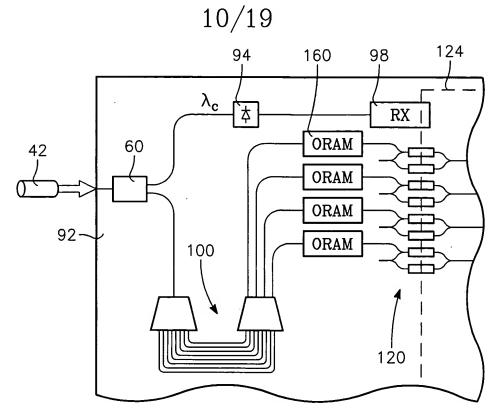


FIG. 18

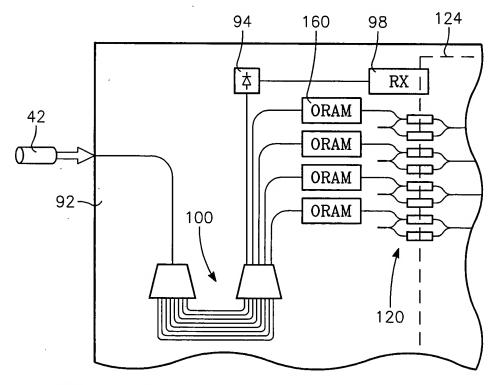
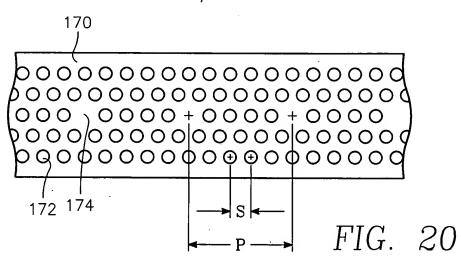
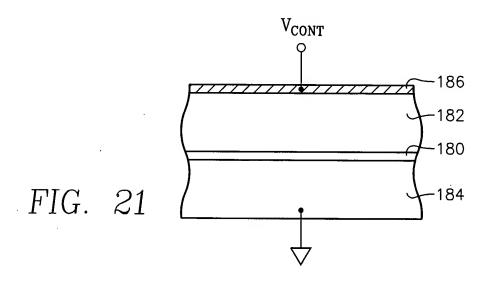
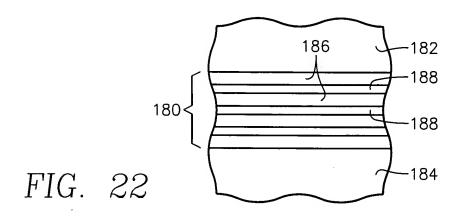


FIG. 19

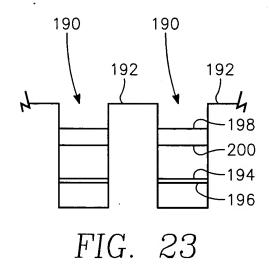








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p-InP

222

4QW i-InGaAsP (1.55 μm)
220

i-InP
218

3QW i-InGaAsP (1.31 μm)
216

n-InP
214

n-InGaAsP (1.25 μm)
212

FIG. 26

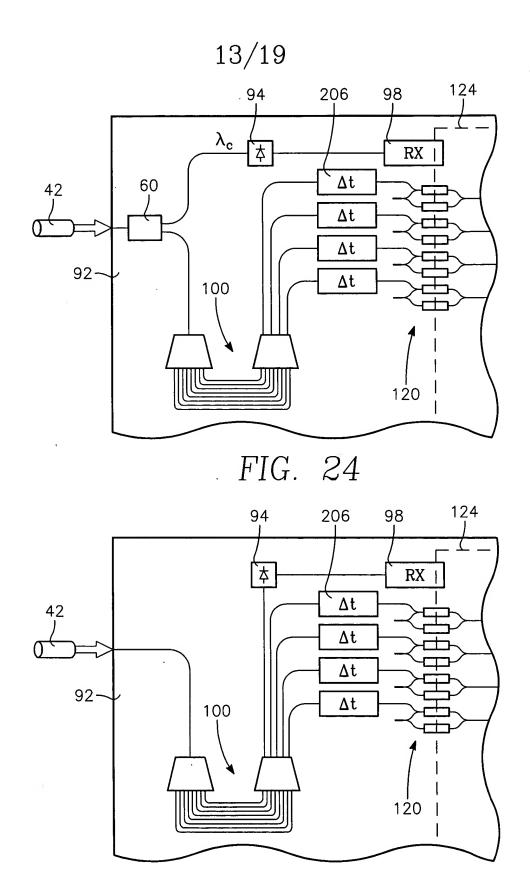


FIG. 25

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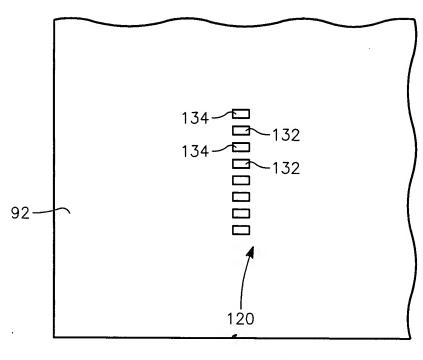


FIG. 27

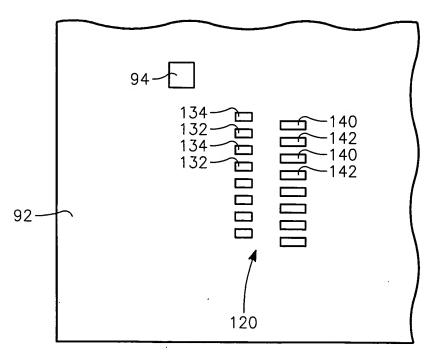


FIG. 28

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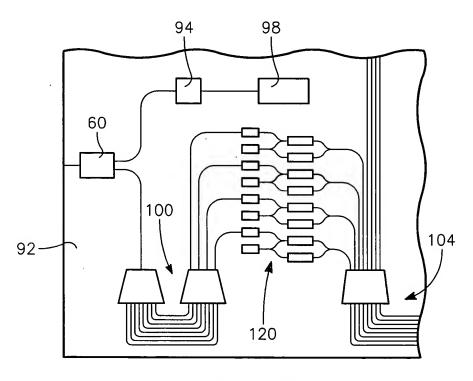
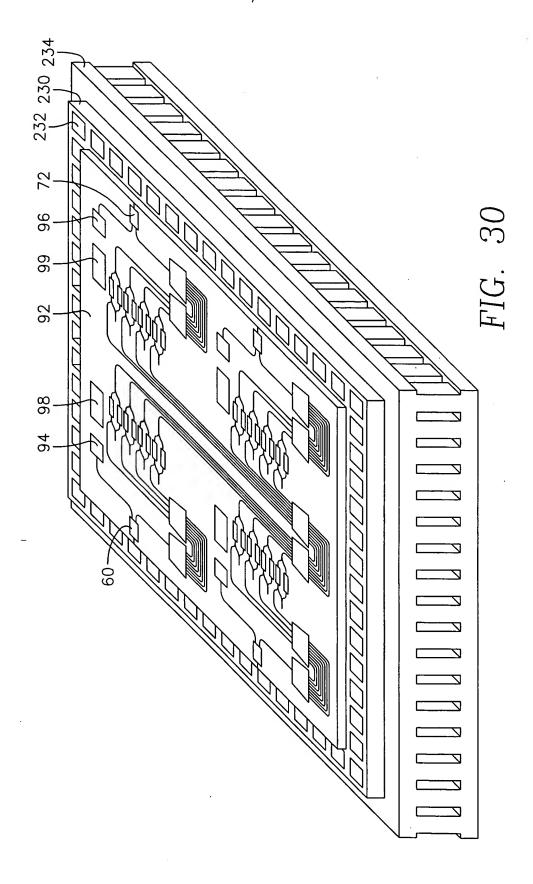
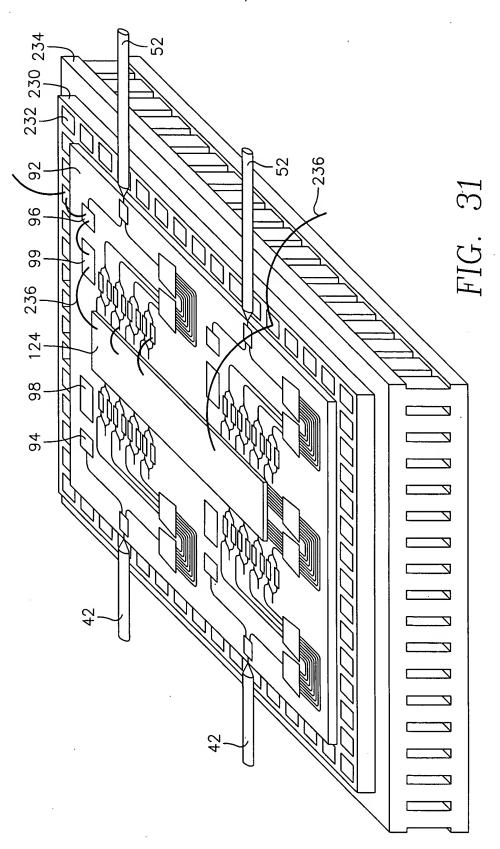


FIG. 29

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